Abstracts

Intermodulation Distortion in GaAs FETs

J.A. Higgins. "Intermodulation Distortion in GaAs FETs." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 138-141.

The influence that the active layer profile plays in determining the Intermodulation Distortion levels (IMD) in a power GaAs FET has been analyzed. A simplified model of a tuned amplifier containing the device sources of nonlinearity has yielded an improved understanding of generation of IMD products in such applications as GaAs FET power amplifiers.

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